

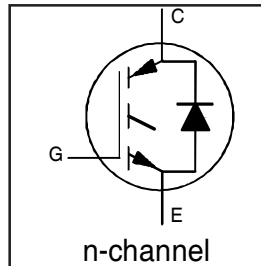
IRG4BC10KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
 ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
 UltraFast IGBT

Features

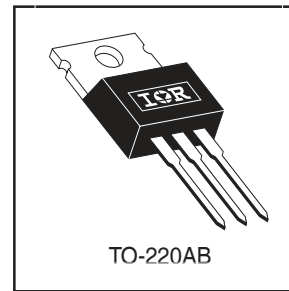
- High short circuit rating optimized for motor control, $t_{sc} = 10\mu s$, @360V V_{CE} (start), $T_J = 125^\circ C$, $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 2.39V$
@ $V_{GE} = 15V, I_C = 5.0A$

Benefits

- Latest generation 4 IGBTs offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	9.0	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	5.0	
I_{CM}	Pulsed Collector Current ①	18	
I_{LM}	Clamped Inductive Load Current ②	18	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	4.0	
I_{FM}	Diode Maximum Forward Current	16	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	38	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	15	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.		
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	3.3	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	7.0	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2 (0.07)	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage _f	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.58	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.39	2.62	V	$I_C = 5.0A$ $V_{GE} = 15V$ See Fig. 2, 5
		—	3.25	—		
		—	2.63	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance „	1.2	1.8	—	S	$V_{CE} = 50V, I_C = 5.0A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
		—	—	1000		
V_{FM}	Diode Forward Voltage Drop	—	1.5	1.8	V	$I_C = 4.0A$ See Fig. 13 $I_C = 4.0A, T_J = 150^\circ\text{C}$
		—	1.4	1.7		
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	19	29	nC	$I_C = 5.0A$ $V_{CC} = 400V$ See Fig.8 $V_{GE} = 15V$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	2.9	4.3		
Q_{gc}	Gate - Collector Charge (turn-on)	—	9.8	15		
$t_{d(on)}$	Turn-On Delay Time	—	49	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$
t_r	Rise Time	—	28	—		
$t_{d(off)}$	Turn-Off Delay Time	—	97	150		
t_f	Fall Time	—	140	210		
E_{on}	Turn-On Switching Loss	—	0.25	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,14
E_{off}	Turn-Off Switching Loss	—	0.14	—		
E_{ts}	Total Switching Loss	—	0.39	0.48		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 100\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	46	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 10,11,14 $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$ Energy losses include "tail" and diode reverse recovery
t_r	Rise Time	—	32	—		
$t_{d(off)}$	Turn-Off Delay Time	—	100	—		
t_f	Fall Time	—	310	—		
E_{ts}	Total Switching Loss	—	0.56	—	mJ	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	220	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
C_{oes}	Output Capacitance	—	29	—		
C_{res}	Reverse Transfer Capacitance	—	7.5	—		
t_{rr}	Diode Reverse Recovery Time	—	28	42	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$ 14
		—	38	57		
I_{rr}	Diode Peak Reverse Recovery Current	—	2.9	5.2	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$ 15
		—	3.7	6.7		
Q_{rr}	Diode Reverse Recovery Charge	—	40	60	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$ 16
		—	70	105		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	280	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$ 17

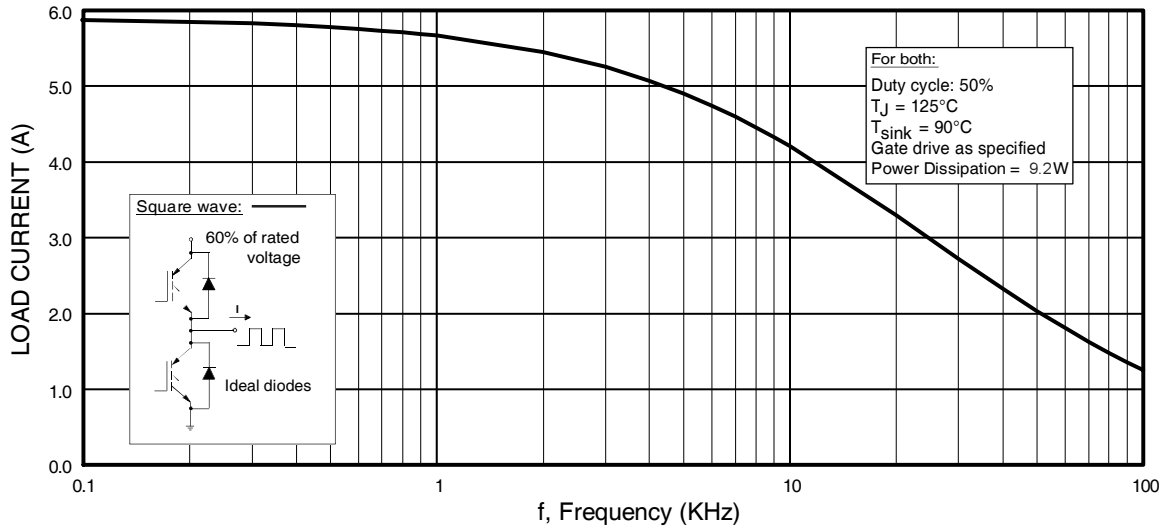


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

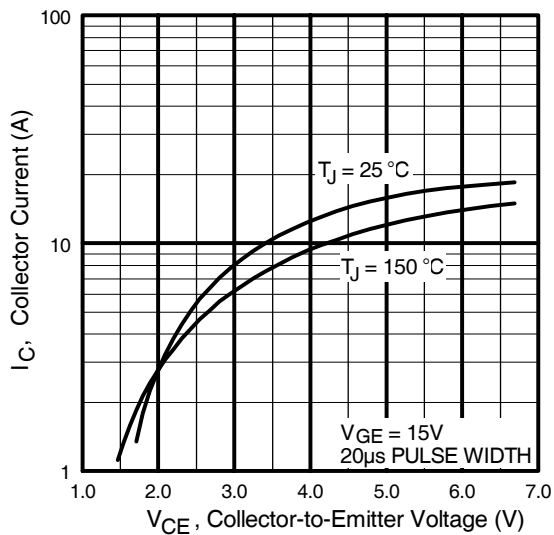


Fig. 2 - Typical Output Characteristics
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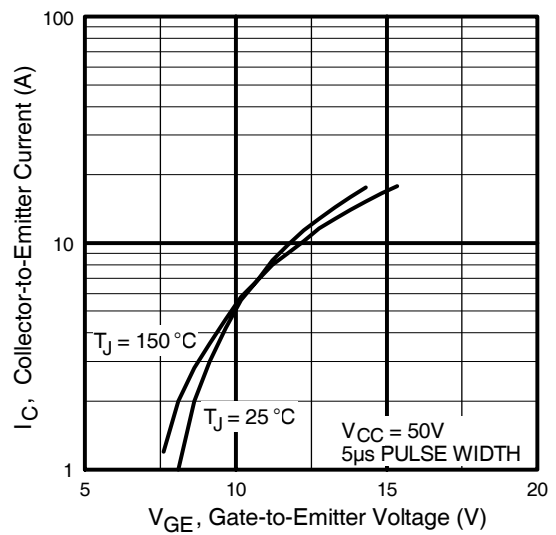


Fig. 3 - Typical Transfer Characteristics

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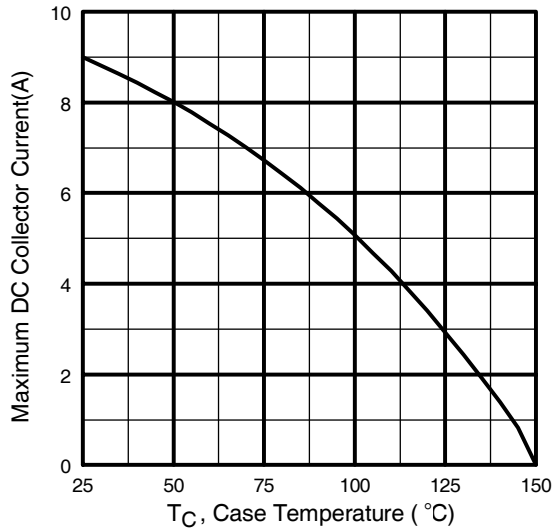


Fig. 4 - Maximum Collector Current vs. Case Temperature

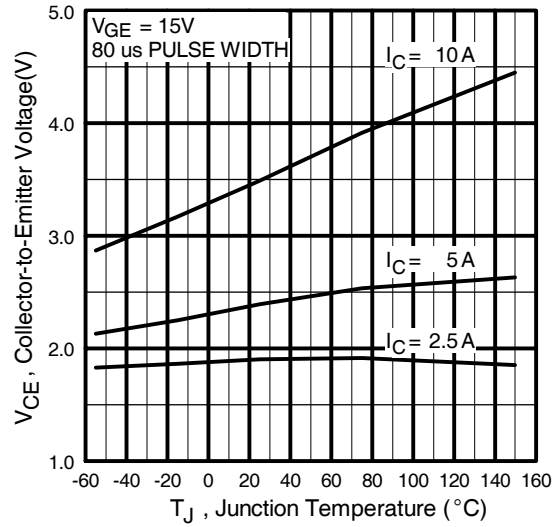


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

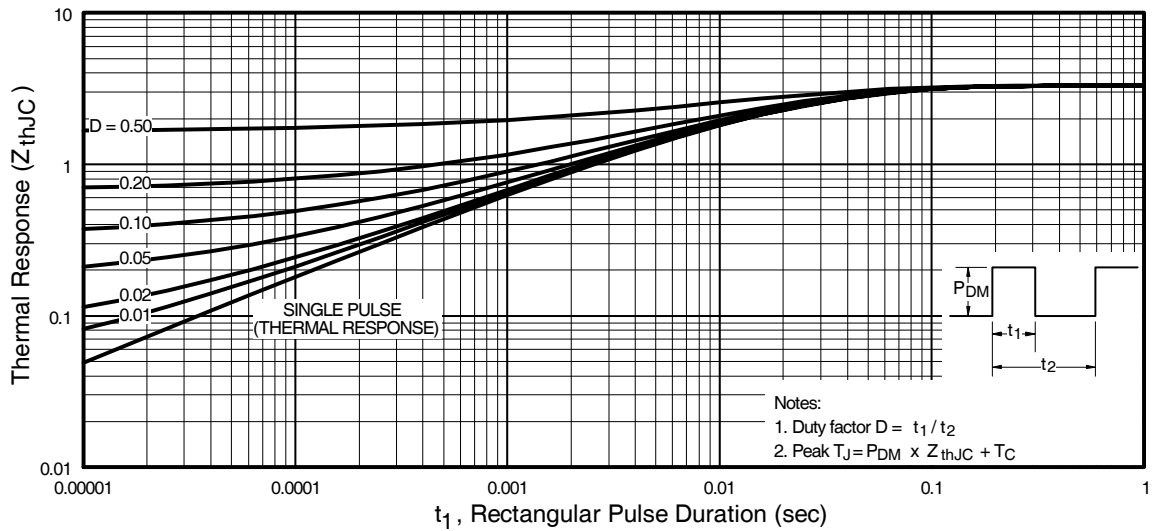


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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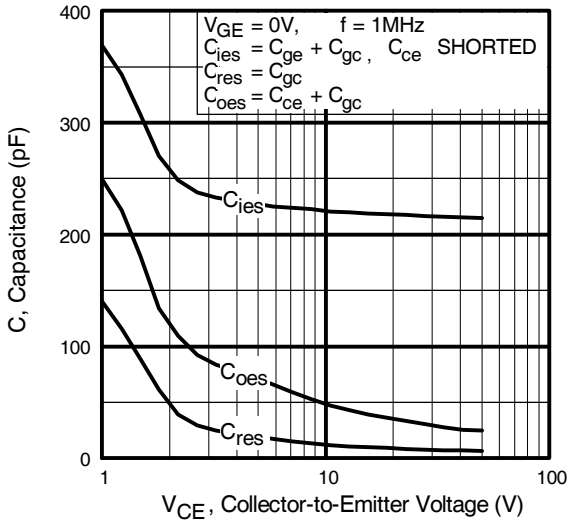


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

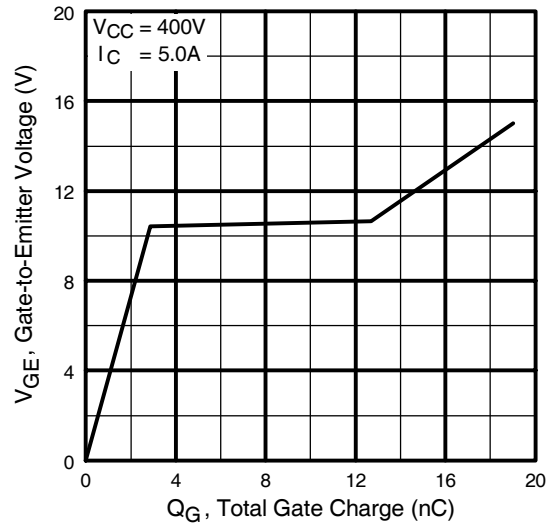


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

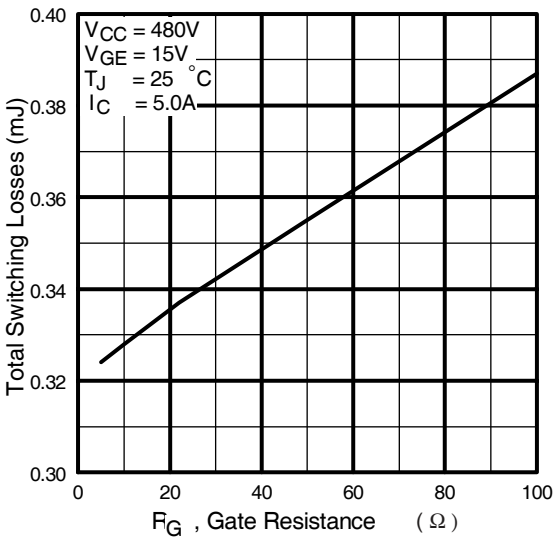


Fig. 9 - Typical Switching Losses vs. Gate Resistance

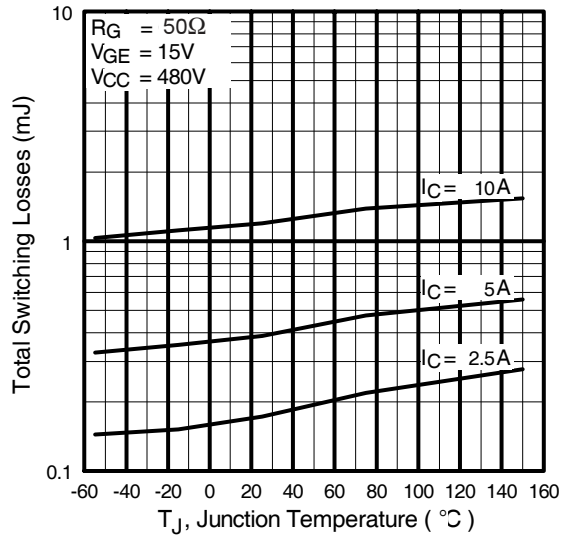


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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IR Rectifier

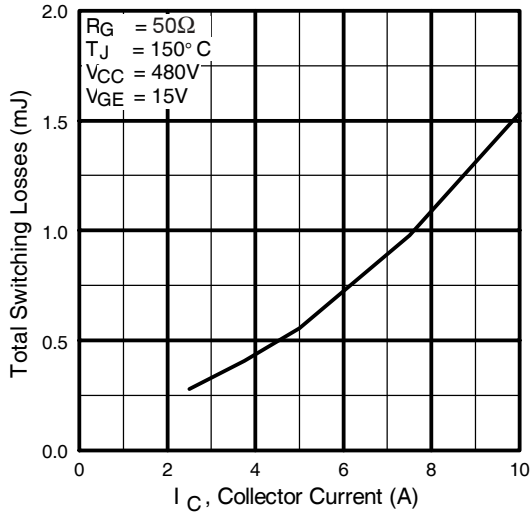


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

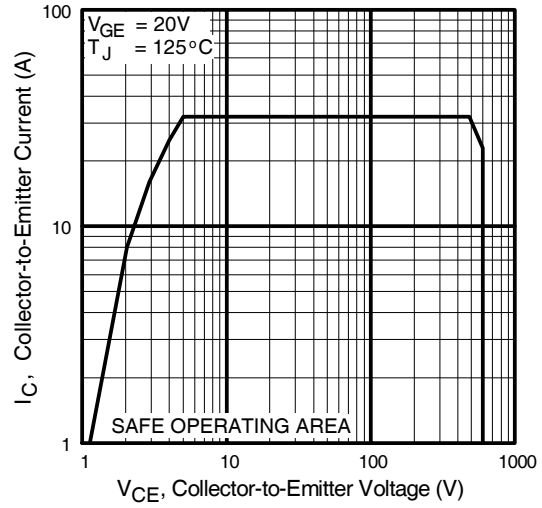


Fig. 12 - Turn-Off SOA

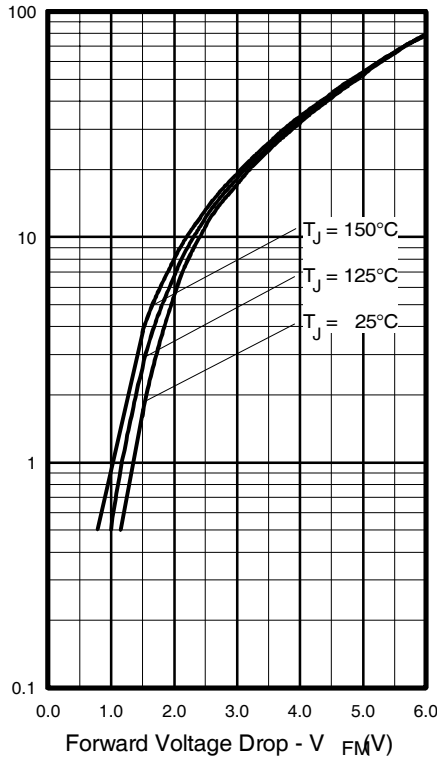


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

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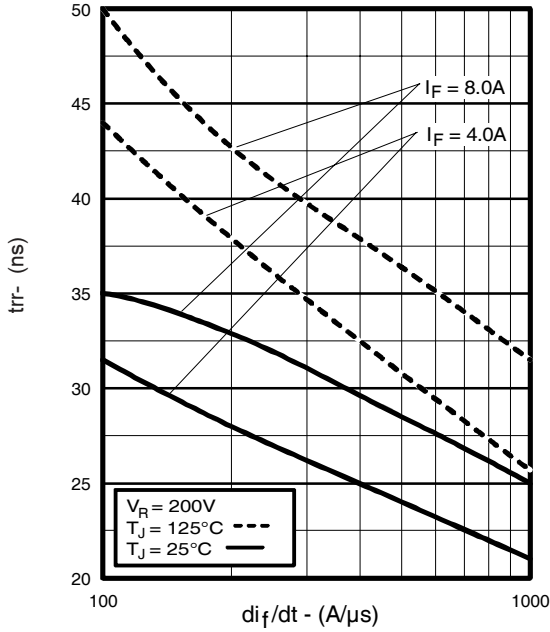


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

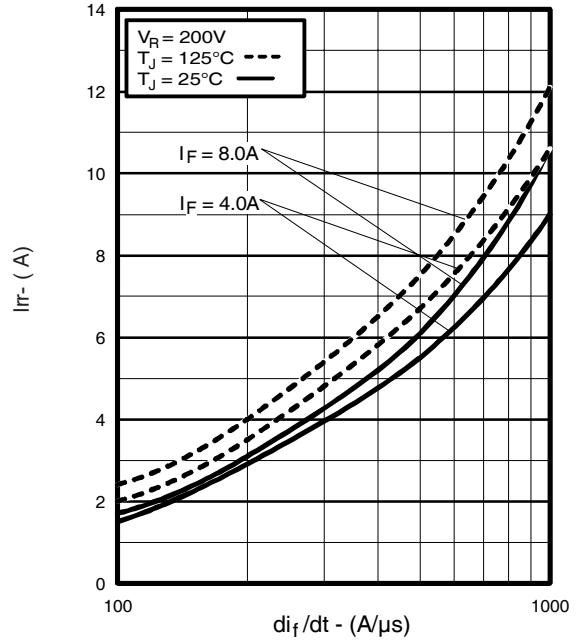


Fig. 15 - Typical Recovery Current vs. di_f/dt

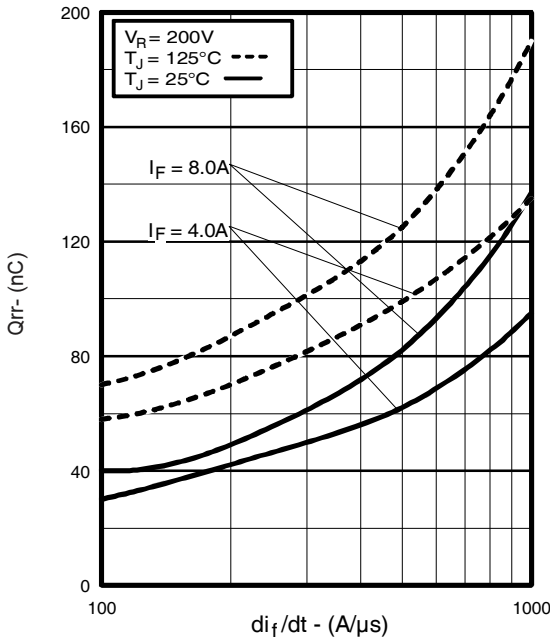


Fig. 16 - Typical Stored Charge vs. di_f/dt

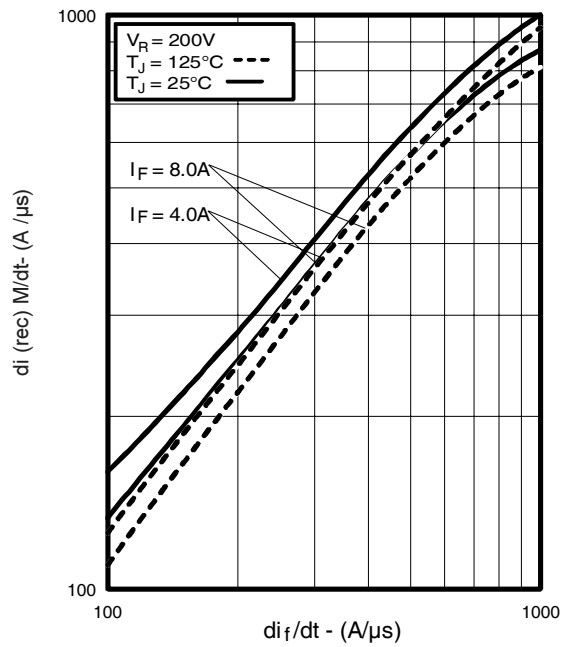


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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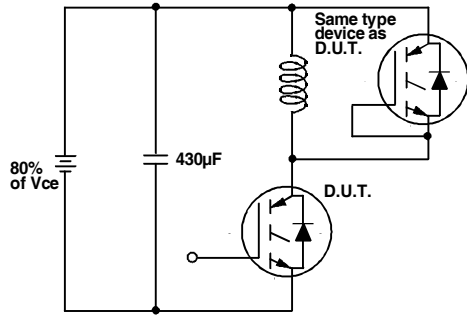


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

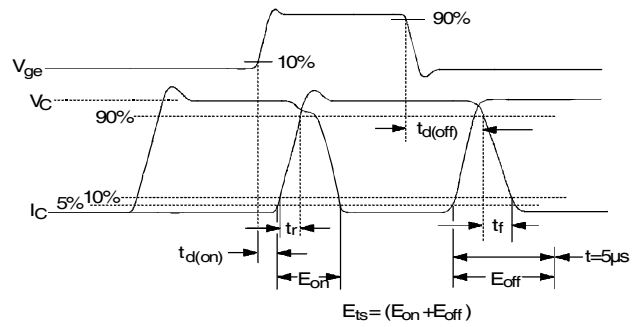


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

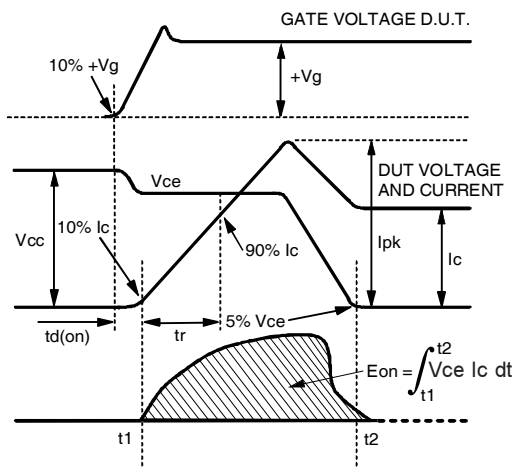


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

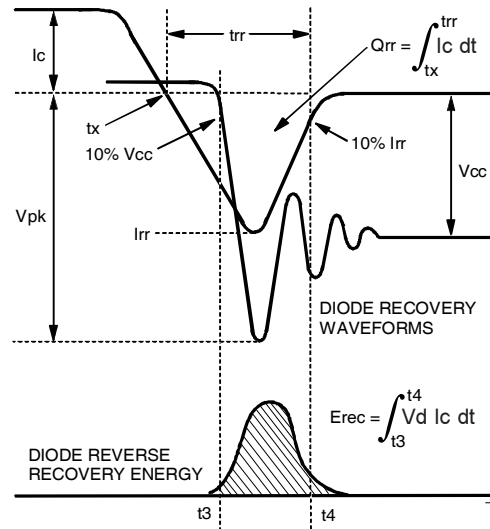


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

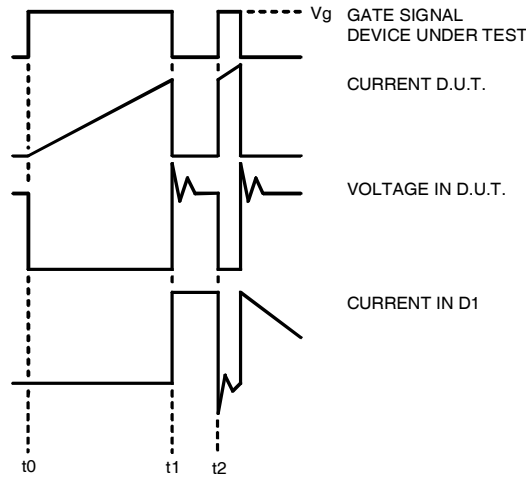


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

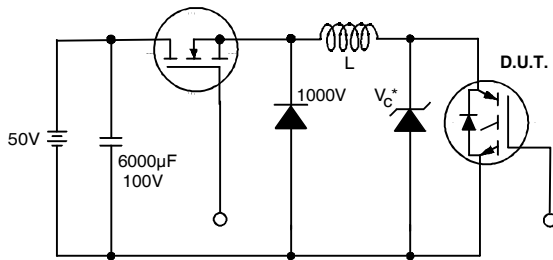


Figure 19. Clamped Inductive Load Test Circuit

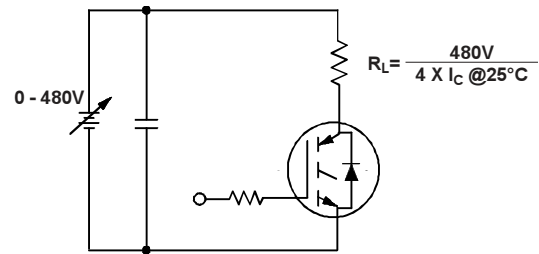


Figure 20. Pulsed Collector Current Test Circuit

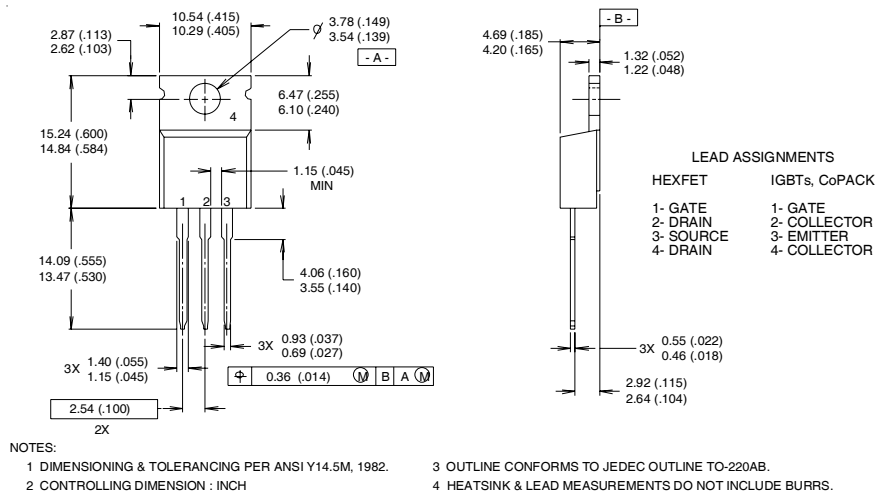
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Notes:

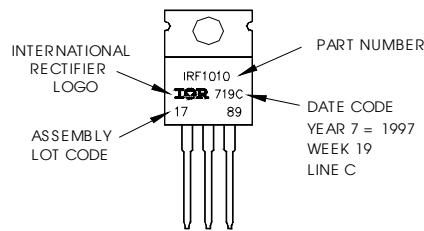
- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=100\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

TO-220AB Package Outline



TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.



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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>